

/ Descriptions

SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

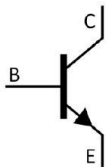
/ Features

High power gain, low noise figure, very low intermodulation distortion.

/ Applications

RF wideband amplifiers and oscillators.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

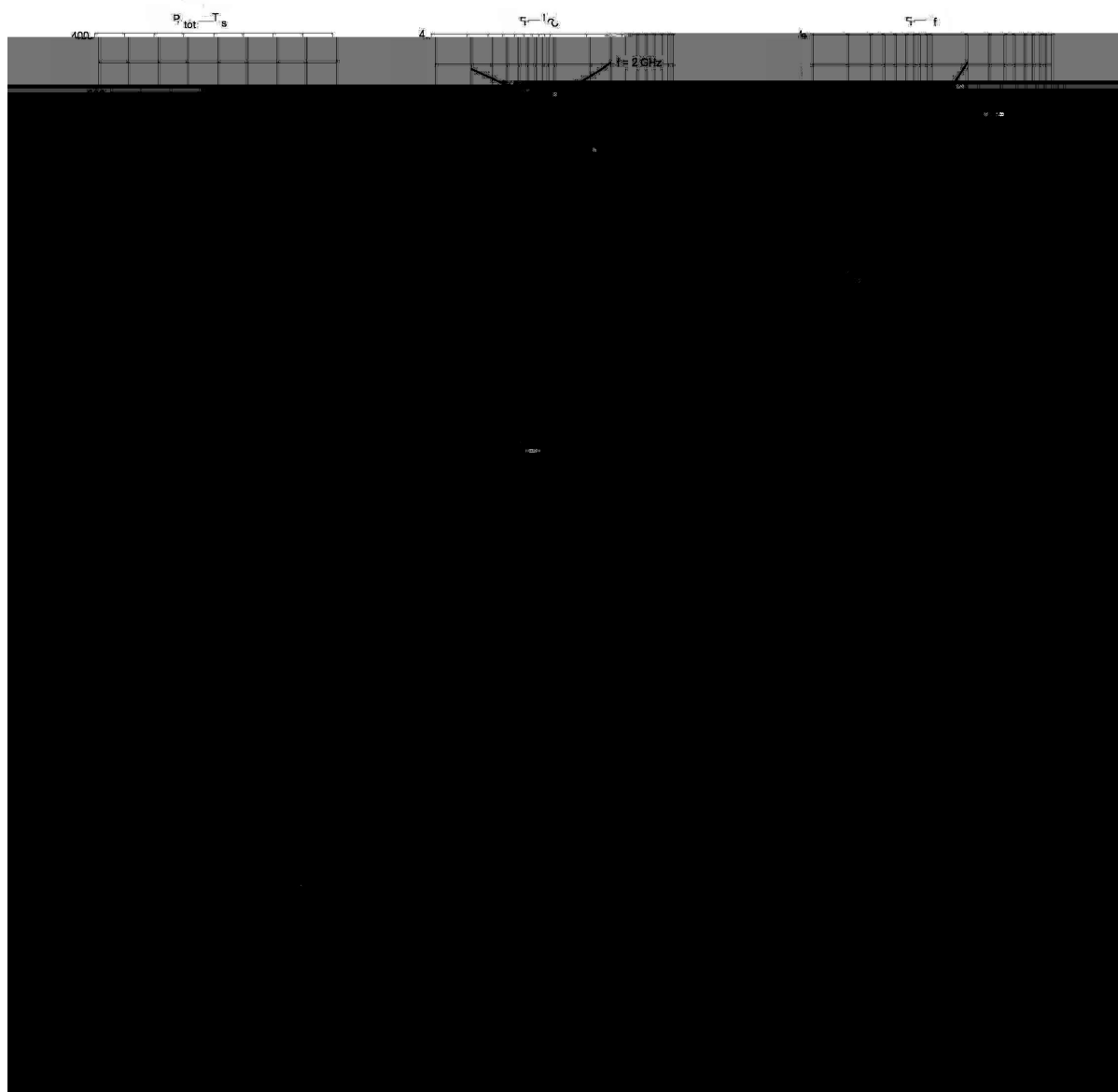
/ Marking

h_{FE} Range	>40
Marking	HR2P

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	15	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	2.0	V
Collector Current - Continuous	I_C	35	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min
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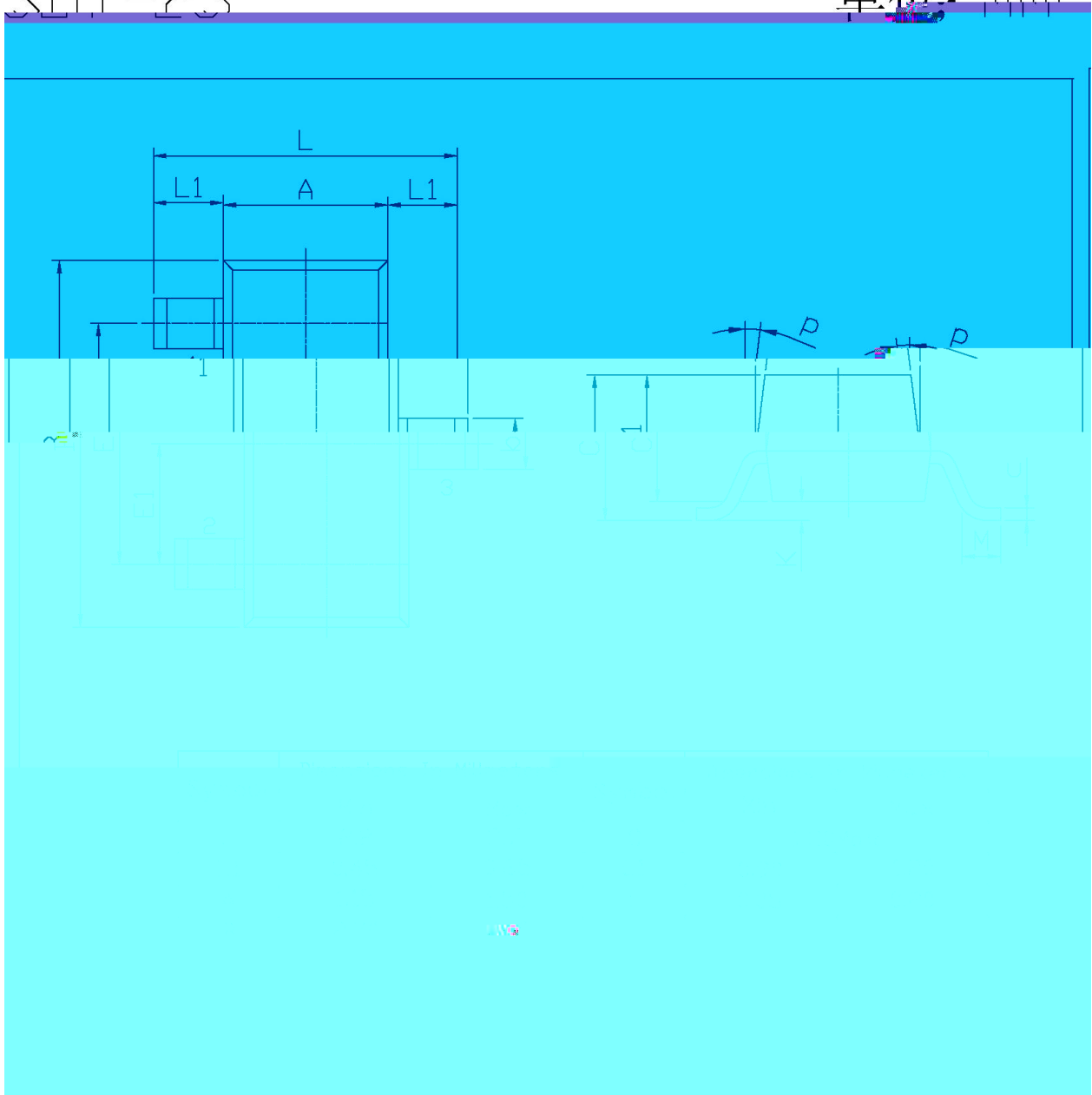
/ Electrical Characteristic Curve



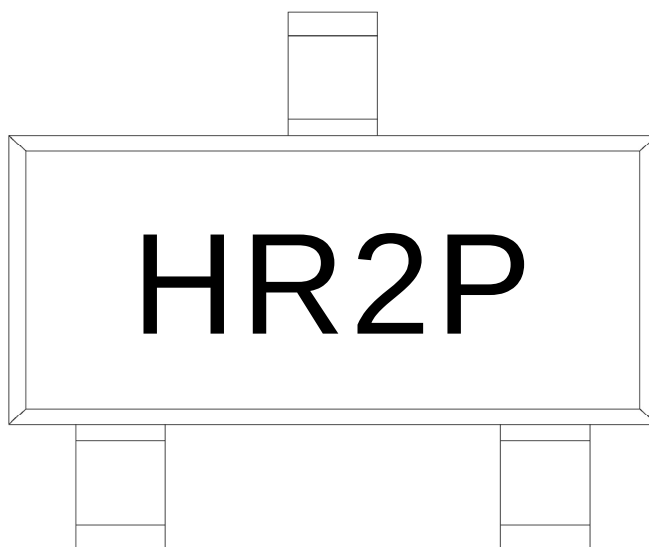
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



H

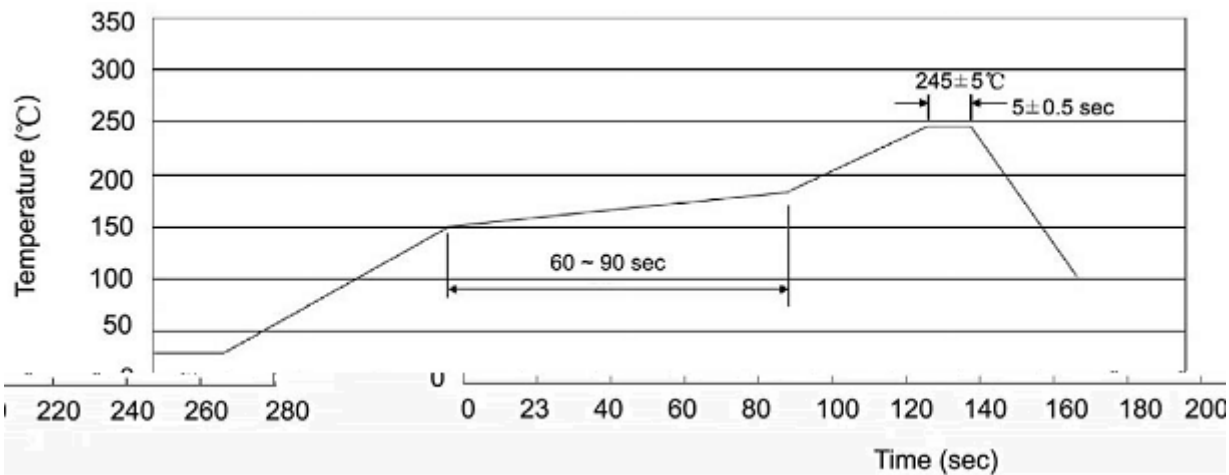
2RP

Note:

H: Company Code.

2RP: Product Type Code.

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Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

/ Notices